HAF1002(L), HAF1002(S)

Silicon P Channel MOS FET Series
Power Switching

HITACHI

ADE-208-586 (Z)
1st. Edition
October 1997

Features

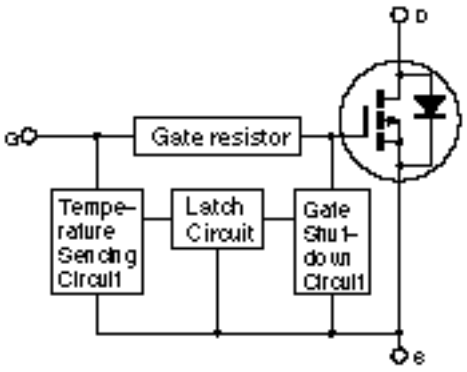
This FET has the over temperature shut–down capability sensing to the junction temperature.

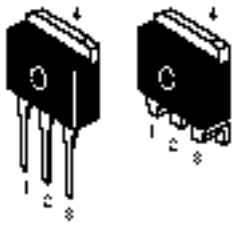
This FET has the built–in over temperature shut–down circuit in the gate area. And this circuit operation to shut–down the gate voltage in case of high junction temperature like applying over power consumption, over current etc.

- Logic level operation (–4 to –6 V Gate drive)
- High endurance capability against to the short circuit
- Built–in the over temperature shut–down circuit
- Latch type shut–down operation (Need 0 voltage recovery)

Outline

LD PAK





1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	–60	V
Gate to source voltage	V_{GSS}	–16	V
Gate to source voltage	V_{GSS}	3	V
Drain current	I_D	–15	A
Drain peak current	$I_{D(pulse)}$ Note1	–30	A
Body-drain diode reverse drain current	I_{DR}	–15	A
Channel dissipation	Pch Note2	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: 1. PW ≤ 10µs, duty cycle ≤ 1 %
2. Value at Tc = 25°C

Typical Operation Characteristics

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V_{IH}	–3.5	—	—	V	
	V_{IL}	—	—	–1.2	V	
Input current	I_{IH1}	—	—	–100	µA	Vi = –8V, V_{DS} = 0
(Gate non shut down)	I_{IH2}	—	—	–50	µA	Vi = –3.5V, V_{DS} = 0
	I_{IL}	—	—	–1	µA	Vi = –1.2V, V_{DS} = 0
Input current	$I_{IH(sd)1}$	—	–0.8	—	mA	Vi = –8V, V_{DS} = 0
(Gate shut down)	$I_{IH(sd)2}$	—	–0.35	—	mA	Vi = –3.5V, V_{DS} = 0
Shut down temperature	T_{sd}	—	175	—	°C	Channel temperature
Gate operation voltage	V_{OP}	–3.5	—	–13	V	

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I_{D1}	–7	—	—	A	V_{GS} = –3.5V, V_{DS} = –2V
Drain current	I_{D2}	—	—	–10	mA	V_{GS} = –1.2V, V_{DS} = –2V
Drain to source breakdown voltage	$V_{(BR)DSS}$	–60	—	—	V	I_D = –10mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	–16	—	—	V	I_G = –100µA, V_{DS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	3	—	—	V	I_G = 100µA, V_{DS} = 0
Gate to source leak current	I_{GSS1}	—	—	–100	µA	V_{GS} = –8V, V_{DS} = 0
	I_{GSS2}	—	—	–50	µA	V_{GS} = –3.5V, V_{DS} = 0
	I_{GSS3}	—	—	–1	µA	V_{GS} = –1.2V, V_{DS} = 0
	I_{GSS4}	—	—	100	µA	V_{GS} = 2.4V, V_{DS} = 0
Input current (shut down)	$I_{GS(op)1}$	—	–0.8	—	mA	V_{GS} = –8V, V_{DS} = 0
	$I_{GS(op)2}$	—	–0.35	—	mA	V_{GS} = –3.5V, V_{DS} = 0
Zero gate voltege drain current	I_{DSS}	—	—	–250	µA	V_{DS} = –50 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	–1.1	—	–2.25	V	I_D = –1mA, V_{DS} = –10V
Static drain to source on state resistance	$R_{DS(on)}$	—	100	130	mΩ	I_D = –7.5A, V_{GS} = –4V Note3
Static drain to source on state resistance	$R_{DS(on)}$	—	70	90	mΩ	I_D = –7.5A V_{GS} = –10V Note3
Forward transfer admittance	$\|y_{fs}\|$	5	10	—	S	I_D = –7.5A, V_{DS} = –10V Note3
Output capacitance	Coss	—	610	—	pF	V_{DS} = –10V , V_{GS} = 0 f = 1 MHz
Turn-on delay time	$t_{d(on)}$	—	7.5	—	µs	I_D = –7.5A, V_{GS} = –5V R_L = 4Ω
Rise time	t_r	—	36	—	µs	
Turn-off delay time	$t_{d(off)}$	—	32	—	µs	
Fall time	t_f	—	29	—	µs	
Body–drain diode forward voltage	V_{DF}	—	–1.0	—	V	I_F = –15A, V_{GS} = 0
Body–drain diode reverse recovery time	t_{rr}	—	200	—	ns	I_F = –15A, V_{GS} = 0 diF/ dt =50A/µs
Over load shut down operation time Note4	t_{os1}	—	3.7	—	ms	V_{GS} = –5V, V_{DD} = –12V
	t_{os2}	—	1	—	ms	V_{GS} = –5V, V_{DD} = –24V

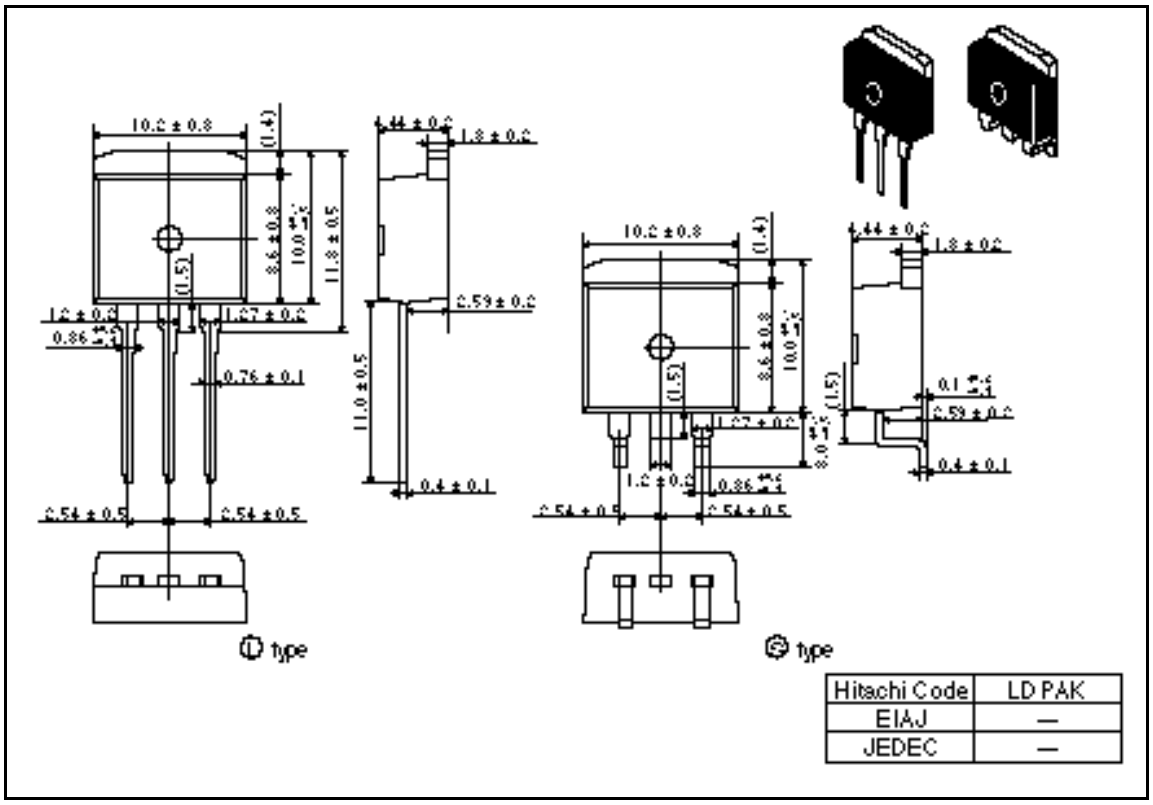
Note: 3. Pulse test

4. Include the time shift based on increasing of channel temperature when operate under over load condition.

See characteristics curve of HAF1001.

Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U.S.A.
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30-00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 01628-585000
Fax: 01628-585160

Hitachi Asia Pte. Ltd.
#5 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071